

Supplementary Information

Precise Control of the Number of Layers of Graphene by Picosecond Laser Thinning

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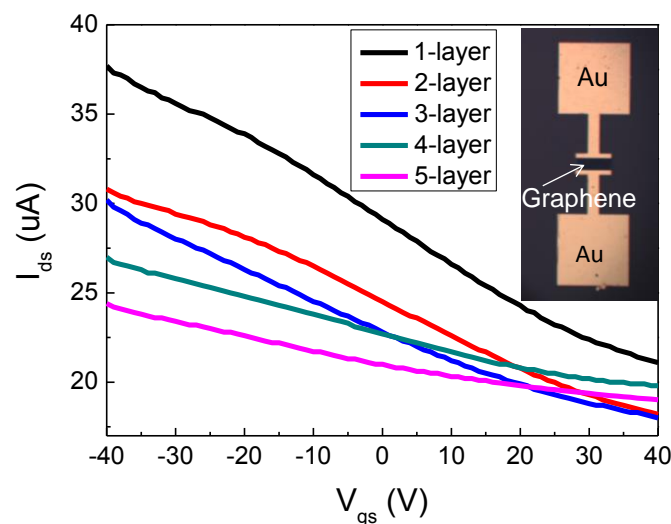


Figure S1. Source-drain current vs. gate voltage plots from graphene FETs of different number of layers. The channel length is 30 μm . The inset shows the optical image of a FET device.